
PART NUMBER**93L422ADMB-ROCS**

Rochester Electronics**Manufactured Components**

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All re-creations are done with the approval of the Original Component Manufacturer. (OCM)

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
 - Class Q Military
 - Class V Space Level

Qualified Suppliers List of Distributors (QSLD)

- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OCM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

National Semiconductor is now part of
Texas Instruments.

Search <http://www.ti.com/> for the latest technical
information and details on our current products and services.



93L422A 256 x 4-Bit Static Random Access Memory

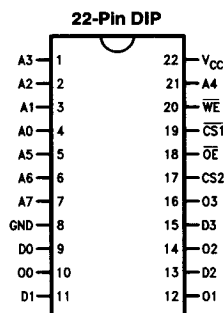
General Description

The 93L422A is a 1024-bit read/write Random Access Memory (RAM) organized 256 words by four bits. It is designed for high speed cache, control and buffer storage applications. The device includes full on-chip decoding, separate Data input and non-inverting Data output, as well as two Chip Select Lines.

Features

- New design to replace old 93422/93L422
- Improved ESD thresholds
- Alpha hard without die coat
- Commercial address access time 93L422A 25 ns
- Fully TTL compatible
- Features TRI-STATE® outputs
- Power dissipation decreases with increasing temperature

Connection Diagram



TL/D/9996-1

Top View

Order Number 93L422ADC or 93L422APC
See NS Package Number J22A* or N22A*

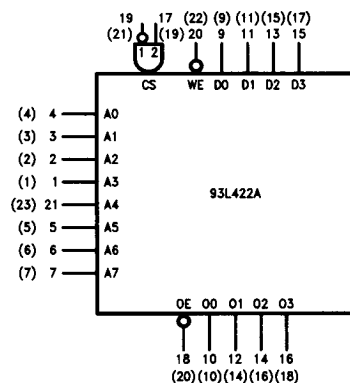
Optional Processing QR = Burn-In

*For most current package information, contact product marketing

Pin Names

A0–A7	Address Inputs
D0–D3	Data Inputs
$\overline{CS}1$	Chip Select Input (Active LOW)
CS2	Chip Select Input (Active HIGH)
$\overline{WE}$	Write Enable Input (Active LOW)
$\overline{OE}$	Output Enable Input (Active LOW)
O0–O3	Data Outputs

Logic Symbol



TL/D/9996-3

Absolute Maximum Ratings

Above which the useful life may be impaired

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	−65°C to +150°C
Supply Voltage Range	−0.5V to +7.0V
Input Voltage (DC) (Note 1)	−0.5V to V_{CC}
Input Current (DC)	−12 mA to +5.0 mA
Voltage Applied to Outputs (Note 2)	−0.5V to +5.5V
Lead Temperature (Soldering, 10 sec.)	300°C
Maximum Junction Temperature (T_J)	+175°C
Output Current	+20 mA

Guaranteed Operating Ranges

Supply Voltage (V_{CC})	5.0V $\pm$ 5%
Case Temperature (T_C)	0°C to +75°C

DC Characteristics over operating temperature ranges (Note 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{OL}	Output LOW Voltage	$V_{CC} = \text{Min}$, $I_{OL} = 8 \text{ mA}$		0.3	0.45	V
V_{IH}	Input HIGH Voltage	Guaranteed Input HIGH Voltage for All Inputs (Notes 4, 5 & 6)	2.1			
V_{IL}	Input LOW Voltage	Guaranteed Input LOW Voltage for All Inputs (Notes 4, 5 & 6)			0.8	
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{Min}$, $I_{OH} = -5.2 \text{ V}$	2.4			V
I_{IL}	Input LOW Current	$V_{CC} = \text{Max}$, $V_{IN} = 0.4 \text{ V}$		−150	−300	μA
I_{IH}	Input HIGH Current	$V_{CC} = \text{Max}$, $V_{IN} = 4.5 \text{ V}$		1.0	40	μA
I_{IHB}	Input Breakdown Current	$V_{CC} = \text{Max}$, $V_{IN} = V_{CC}$			1.0	mA
V_{IC}	Input Diode Clamp Voltage	$V_{CC} = \text{Max}$, $I_{IN} = -10 \text{ mA}$		−1.0	−1.5	V
I_{OZH}	Output Current (HIGH Z)	$V_{CC} = \text{Max}$, $V_{OUT} = 2.4 \text{ V}$			50	μA
I_{OZL}		$V_{CC} = \text{Max}$, $V_{OUT} = 0.5 \text{ V}$			−50	μA
I_{OS}	Output Current Short Circuit to Ground	$V_{CC} = \text{Max}$ (Note 7)	−10		−70	mA
I_{CC}	Power Supply Current	$V_{CC} = \text{Max}$, All Outputs Open, All Inputs = GND			80	mA

AC Electrical Characteristics (Note 6) $V_{CC} = 5.0V \pm 5\%$, $GND = 0V$, $T_C = 0^\circ C$ to $+75^\circ C$

Symbol	Parameter	Conditions	Min	Max	Units
READ TIMING					
t _{ACS}	Chip Select Access Time	Figures 3a, 3b, 3c		20	ns
t _{ZRCS}	Chip Select to High Z			20	ns
t _{AOS}	Output Enable Access Time			20	ns
t _{ZROS}	Output Enable to HIGH Z			20	ns
t _{AA}	Address Access Time (Note 8)			25	ns
WRITE TIMING					
t _W	Write Pulse Width to Guarantee Writing (Note 9)	Figure 4	20		ns
t _{WSD}	Data Setup Time prior to Write		5		ns
t _{WHD}	Data Hold Time after Write		5		ns
t _{WSA}	Address Setup Time prior to Write (Note 9)		5		ns
t _{WHA}	Address Hold Time after Write		5		ns
t _{WSCS}	Chip Select Setup Time prior to Write		5		ns
t _{WHCS}	Chip Select Hold Time after Write		5		ns
t _{ZWS}	Write Enable to Output Disable			20	ns
t _{WR}	Write Recovery Time			20	ns

Note 1: Either input voltage limit or input current limit sufficient to protecting inputs.

Note 2: Output current limit required.

Note 3: Typical values are at $V_{CC} = 5.0V$, $t_C = +25^\circ C$ and maximum loading.

Note 4: Static condition only.

Note 5: Functional testing done at input levels $V_{IL} = 0.45V$ (V_{OL} Max) and $V_{IH} = 2.4V$ (V_{OH} Min).

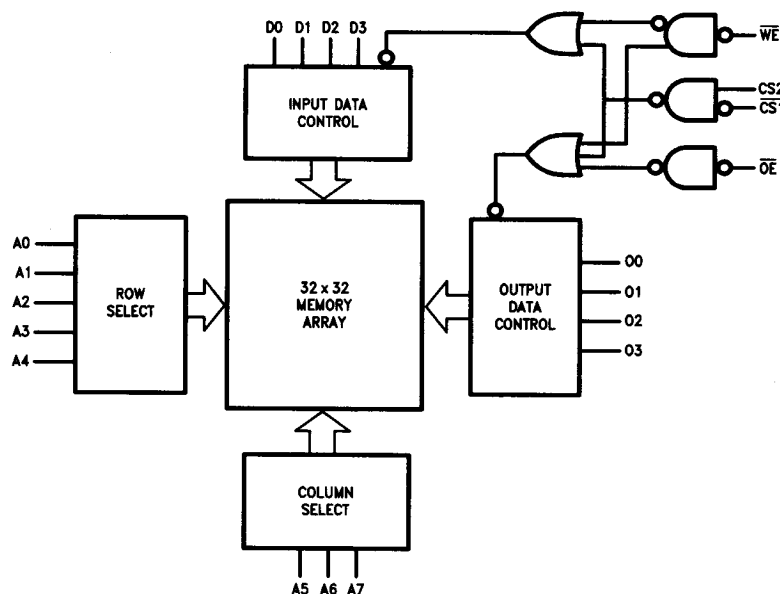
Note 6: AC testing done at input levels $V_{IH} = 3V$, $V_{IL} = 0V$.

Note 7: Short circuit to ground not to exceed one second; ground only one output at a time.

Note 8: The maximum address access time is guaranteed to be the worst case bit in the memory using a pseudorandom testing pattern.

Note 9: t_W measured at $t_{WSA} = \text{Min}$. t_{WSA} measured at $t_W = \text{Min}$.

Logic Diagram



TL/D/9996-2

Truth Table

Inputs				Outputs	Mode
OE	CS1	CS2	WE	TRI-STATE	
X	H	X	X	HIGH Z	Not Selected
X	X	L	X	HIGH Z	Not Selected
L	L	H	H	DOUT	READ
X	L	H	L	HIGH Z	WRITE
H	X	X	X	HIGH Z	Output Disabled

H = HIGH Voltage Level 2.4V
 L = LOW Voltage Level 0.45V
 X = Don't Care HIGH or LOW
 HIGH Z = High-Impedance

Functional Description

The 93L422A is a fully decoded 1024-bit Random Access Memory organized 256 words by four bits. Word selection is achieved by means of an 8-bit address A0-A7.

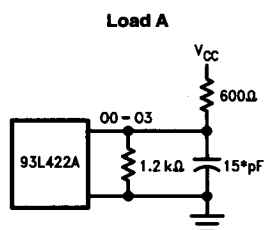
Two Chip Select inputs, inverting and non-inverting, are provided for logic flexibility. For larger memories, the fast chip select access time permits the decoding of the chip selects from the address without increasing address access time.

The read and write operations are controlled by the state of the active LOW Write Enable WE input. When WE is held

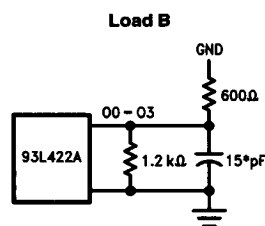
LOW and the chip is selected, the data at D0-D3 is written into the address location. Since the write function is level-triggered, data must be held stable for at least $t_{WSD}(\text{Min})$ plus $t_W(\text{Min})$ plus $t_{WHD}(\text{Min})$ to insure a valid write. To read, WE is held high, the chip is selected, and the data is transferred to the outputs (O0-O3).

The 93L422A has TRI-STATE outputs which provide active pull-ups when enabled and high output impedance when disabled. This allows optimization of word expansion in bus organized systems.

Functional Description (Continued)



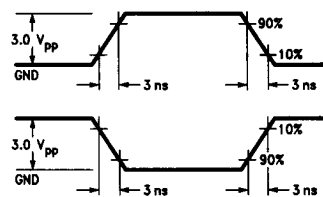
TL/D/9996-4



TL/D/9996-5

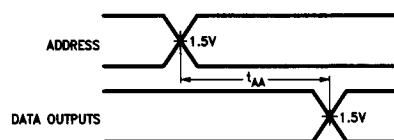
*Includes jig and probe capacitance
 Note: Load A is used for all production testing.

FIGURE 1. AC Test Output Load



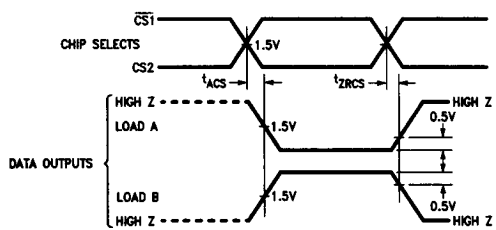
TL/D/9996-6

FIGURE 2. AC Test Input Levels



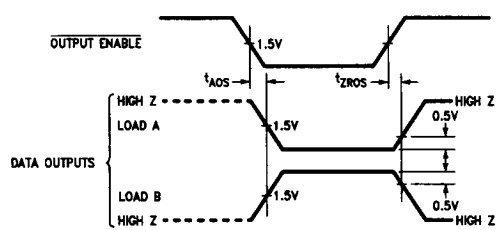
TL/D/9996-7

3a. Read Mode Propagation Delay from Address



TL/D/9996-8

3b. Read Mode Propagation Delay from Chip Select



TL/D/9996-9

3c. Read Mode Propagation Delay from Output Enable

FIGURE 3. Read Mode Testing

Functional Description (Continued)

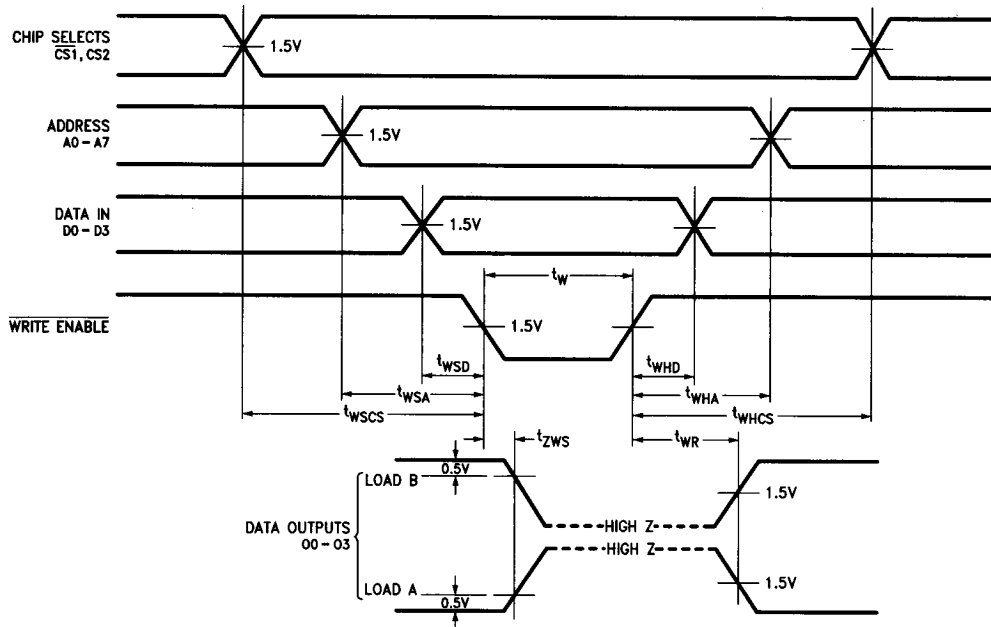


FIGURE 4. Write Mode Timing

TL/D/9996-10

Note 1: Timing Diagram represents one solution which results in an optimum cycle time. Timing may be changed to fit various applications as long as the worst case limits are not violated.

Note 2: Input voltage levels for worst case AC test are 3.0V-0V.